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40F. Ferroelectric Memories

Session Date:	March 9(Thu.), 2023
Session Time:	14:45-16:10
Session Room:	Room F (#317)
Session Chair:	Prof. Jianshi Tang (Tsinghua University) Prof. Si Joon Kim (Kangwon National University)

[40F-1] [Invited]

14:45-15:10

The Top Electrode Tensile Stress Effect on Ferroelectricity of Hf_{0.5}Zr_{0.5}O₂ Thin Films

Runhao Han^{1,2}, Peizhen Hong³, JingWen Hou¹, Wenjuan Xiong¹, Shuai Yang¹, Jianfeng Gao¹ and Zongliang Huo^{1,2,4}

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[40F-2]

15:10-15:25

Performance Evaluation of AFeRAM under Low Temperature Operation

Yi-Chuan Chen¹, Yu-Chen Chen¹, Kuo-Yu Hsiang^{1,2}, Min-Hung Lee² and Pin Su¹

¹National Yang Ming Chiao Tung University, ²National Taiwan Normal University

[40F-3]

15:25-15:40

Energy-Efficient Annealing Process of HfO₂-Based Ferroelectric Capacitor Using UV-LED for Green Manufacturing

Hirotaka Yamada^{1,2}, Satoru Furue¹, Takehiko Yokomori¹, Yuki Itoya², Takuya Saraya², Toshiro Hiramoto² and Masaharu Kobayashi²

¹Ushio Inc, ²The University of Tokyo

[40F-4]

15:40-15:55

Atomic-Scale Study on Amorphous ZrO₂/TaON Interface for Ferroelectric-Like Insulator Films

Zhi Gong¹, Jiajia Chen¹, Chengji Jin¹, Huan Liu¹, Yan Liu², Xiao Yu¹ and Genquan Han²

¹Zhejiang Lab, ²Xidian University

[40F-5]

15:55-16:10

A Study on the Thermal Budget of Ferroelectric TiN/Hf_{0.5}Zr_{0.5}O₂ /TiN Capacitors for Next-Generation Memory Applications

Hyeyeon Park¹, Jeong Gyu Yoo¹, Jong Mook Kang¹, Min Kwan Cho¹, Taeho Gong¹, Seongbin Park¹, Seungbin Lee¹, Jin-Hyun Kim², Seojun Lee^{2,3}, Rino Choi³, Harrison Sejoon Kim², Yong Chan Jung², Jiyoung Kim² and Si Joon Kim¹

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